TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

# 2SC3665

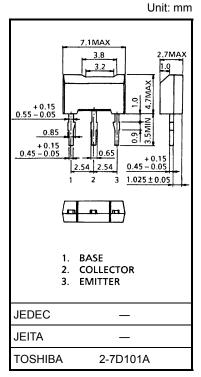
Audio Power Amplifier Applications Driver-Stage Amplifier Applications

• Complementary to 2SA1425.

### **Absolute Maximum Ratings (Ta = 25°C)**

| Characteristics             | Symbol           | Rating     | Unit |
|-----------------------------|------------------|------------|------|
| Collector-base voltage      | $V_{CBO}$        | 120        | V    |
| Collector-emitter voltage   | V <sub>CEO</sub> | 120        | ٧    |
| Emitter-base voltage        | V <sub>EBO</sub> | 5          | ٧    |
| Collector current           | IC               | 800        | mA   |
| Base current                | ΙΒ               | 80         | mA   |
| Collector power dissipation | PC               | 1000       | mW   |
| Junction temperature        | Tj               | 150        | °C   |
| Storage temperature range   | T <sub>stg</sub> | −55 to 150 | °C   |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.



Weight: 0.2 g (typ.)

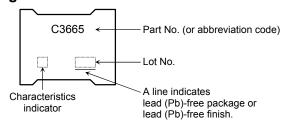
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

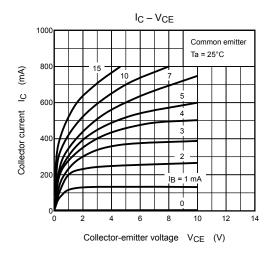
## **Electrical Characteristics (Ta = 25°C)**

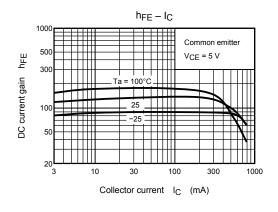
| Characteristics                      | Symbol                    | Test Condition  | Min | Тур. | Max | Unit |
|--------------------------------------|---------------------------|---|-----|------|-----|------|
| Collector cut-off current            | I <sub>CBO</sub>          | V <sub>CB</sub> = 120 V, I <sub>E</sub> = 0           | _   | _    | 100 | nA   |
| Emitter cut-off current              | I <sub>EBO</sub>          | V <sub>EB</sub> = 5 V, I <sub>C</sub> = 0             | _   | _    | 100 | nA   |
| Collector-emitter breakdown voltage  | V (BR) CEO                | I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0            | 120 | -    |     | ٧    |
| Emitter-base breakdown voltage       | V (BR) EBO                | I <sub>E</sub> = 1 mA, I <sub>C</sub> = 0             | 5   | ı    | ı   | >    |
| DC current gain                      | h <sub>FE</sub><br>(Note) | V <sub>CE</sub> = 5 V, I <sub>C</sub> = 100 mA        | 80  |      | 240 |      |
| Collector-emitter saturation voltage | V <sub>CE</sub> (sat)     | I <sub>C</sub> = 500 mA, I <sub>B</sub> = 50 mA       | _   | _    | 1.0 | V    |
| Base-emitter voltage                 | $V_{BE}$                  | V <sub>CE</sub> = 5 V, I <sub>C</sub> = 500 mA        | _   | _    | 1.0 | V    |
| Transition frequency                 | f <sub>T</sub>            | V <sub>CE</sub> = 5 V, I <sub>C</sub> = 100 mA        | _   | 120  | _   | MHz  |
| Collector output capacitance         | C <sub>ob</sub>           | V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz | _   | _    | 30  | pF   |

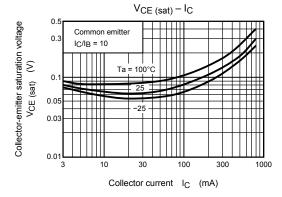
Note: hFE classification O: 80 to 160, Y: 120 to 240

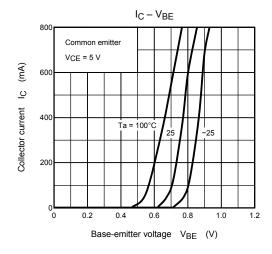
## Marking

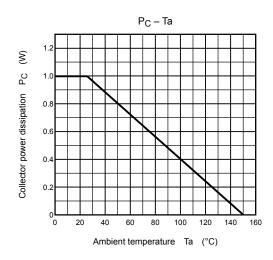


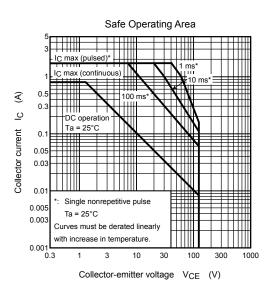












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